

SINGLE WALL CARBON NANOTUBES FOR PRINTED ELECTRONICS

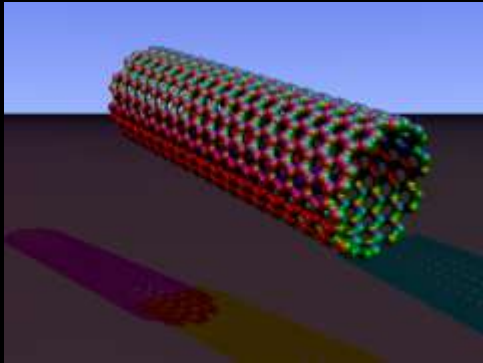
Philip Wallis, SouthWest NanoTechnologies

CONTENTS

- What are Carbon Nanotubes?
 - Properties of Carbon Nanotubes
 - Advantages of Printed Electronics
 - Overcoming Barriers to Adoption
 - Current Status for TCF and TFTs
-

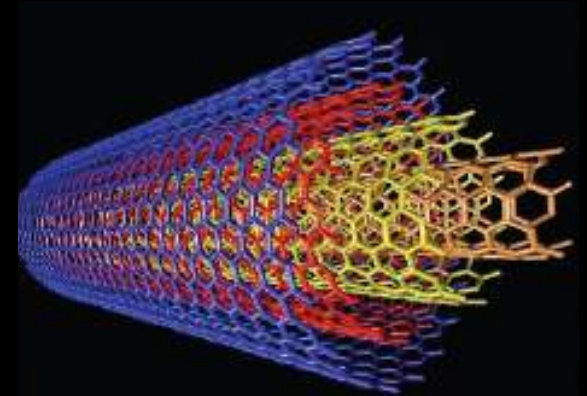
MAJOR CATEGORIES OF CARBON NANOTUBES

Single Wall Carbon Nanotubes
 $d \sim 1 \text{ nm}$



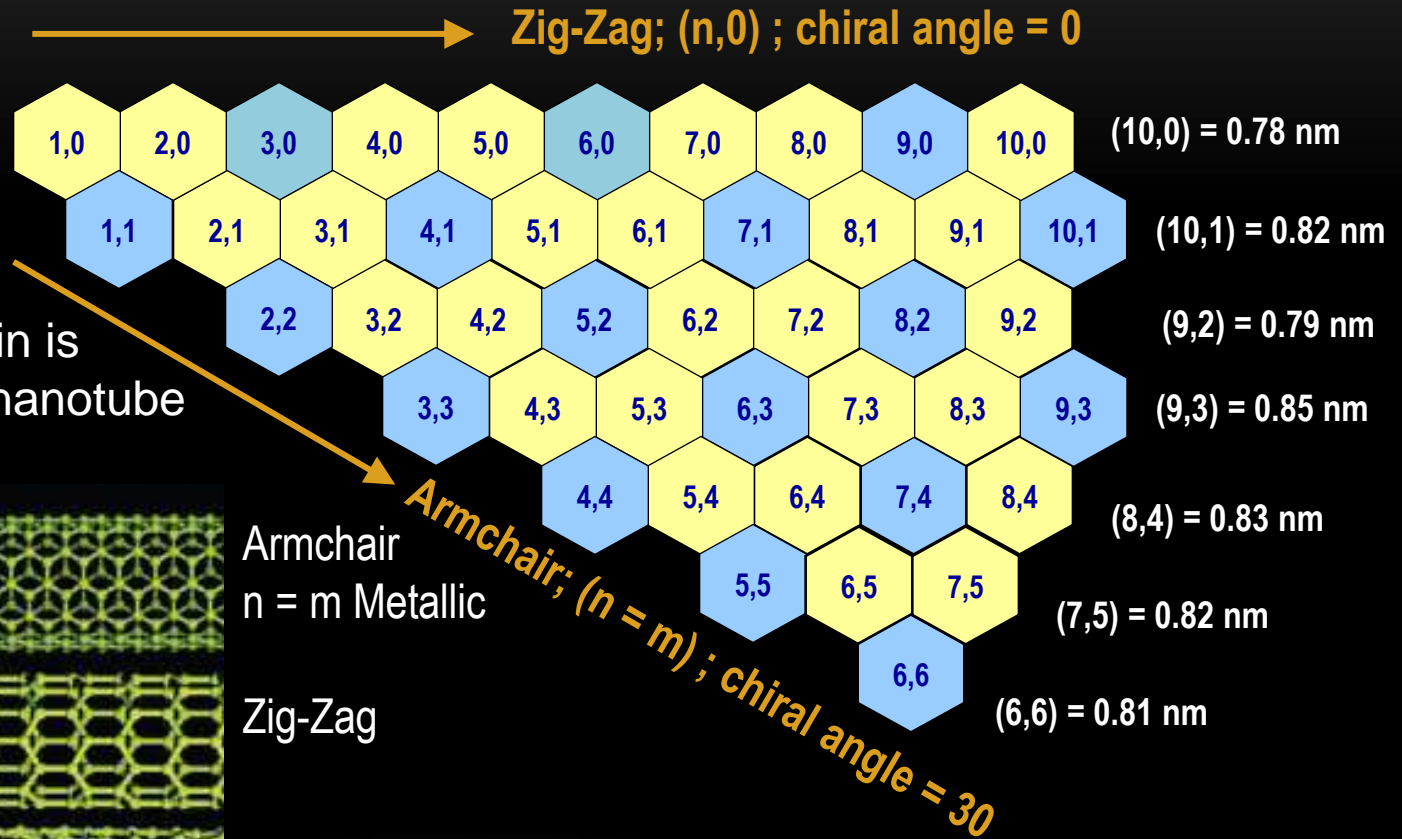
Thin Films for Electronics

Multiwall Carbon nanotubes
 $5 < d < 200 \text{ nm}$

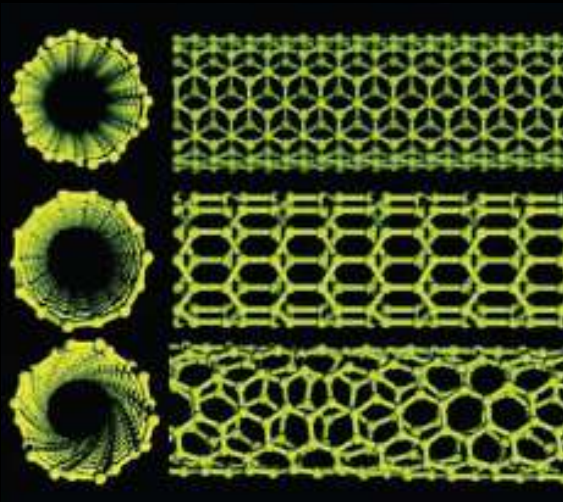


Additives for plastics and resins.

SWCNT CHIRALITY AND DIAMETER



Distance from origin is proportional to nanotube diameter



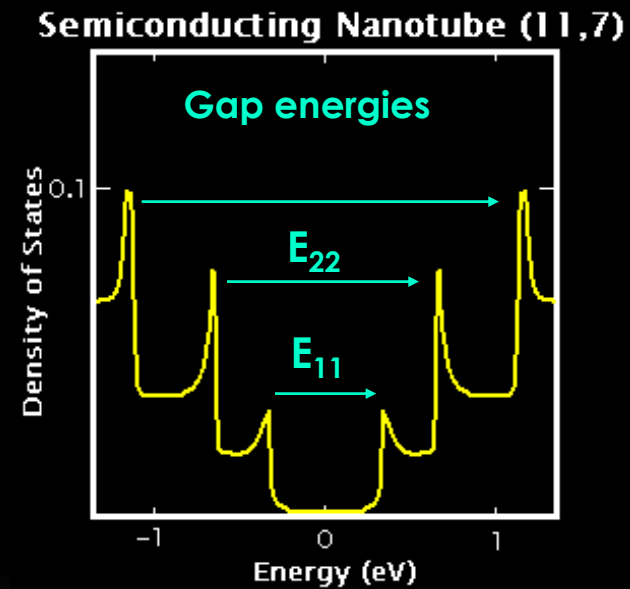
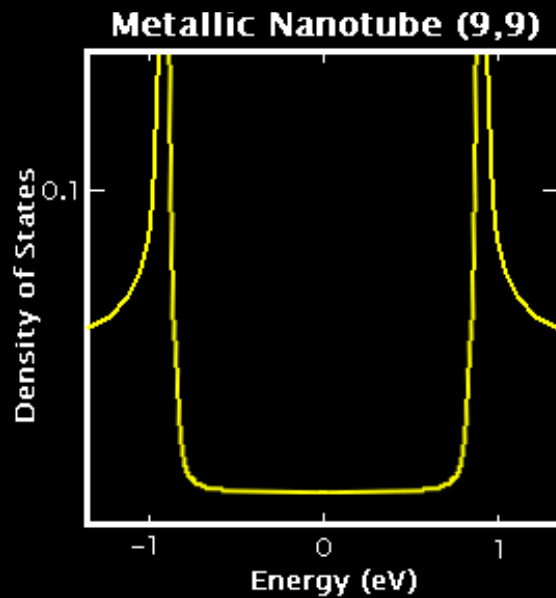
Armchair
 $n = m$ Metallic

Zig-Zag

Chiral

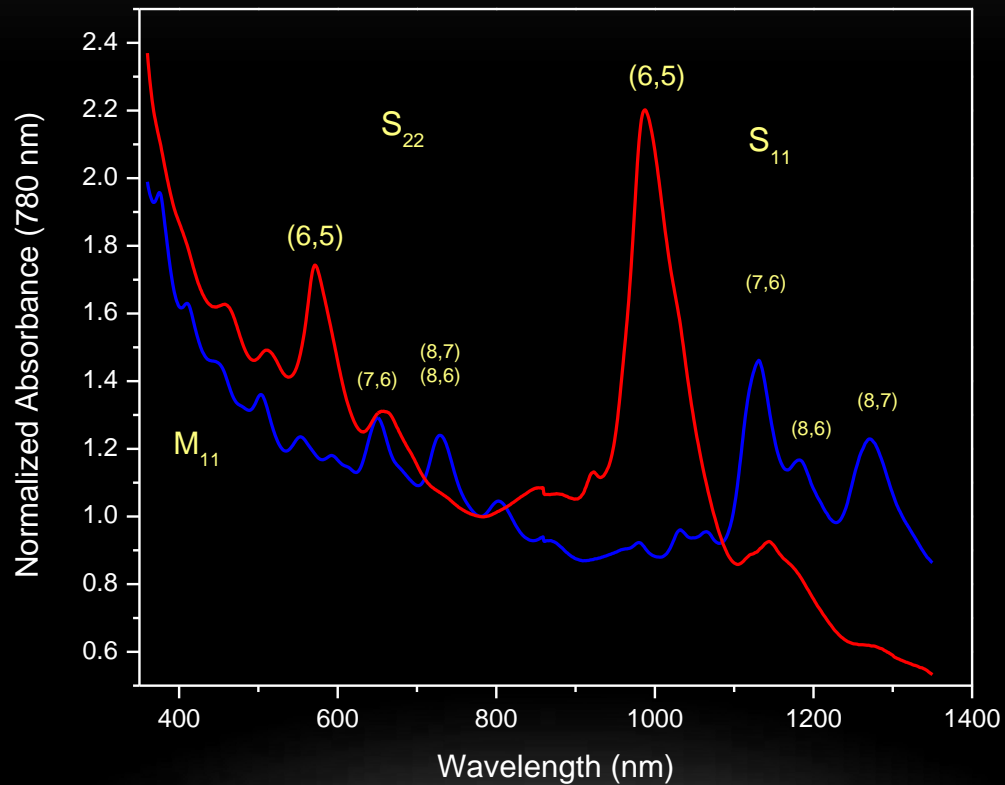
SWCNT DENSITY OF STATES

Metallic tubes have non-zero electron density at the Fermi level.
Semiconducting tubes have zero density and exhibit a band gap.



OPTICAL ABSORBANCE SPECTRA

Optical Absorbance Spectrum for SWeNT[®] SG65 and SG76



WHY CARBON NANOTUBES

- “Discovered” by Iijima in 1991 >20 Years Ago
 - 50X Stronger than Steel
 - More Conductive than Copper
 - $\frac{1}{2}$ Density of Al
 - Metallic or Semiconducting
 - Optically Transparent
-

POTENTIAL APPLICATIONS

Lighting



Touch



Displays



TFTs



Sensors



Solar



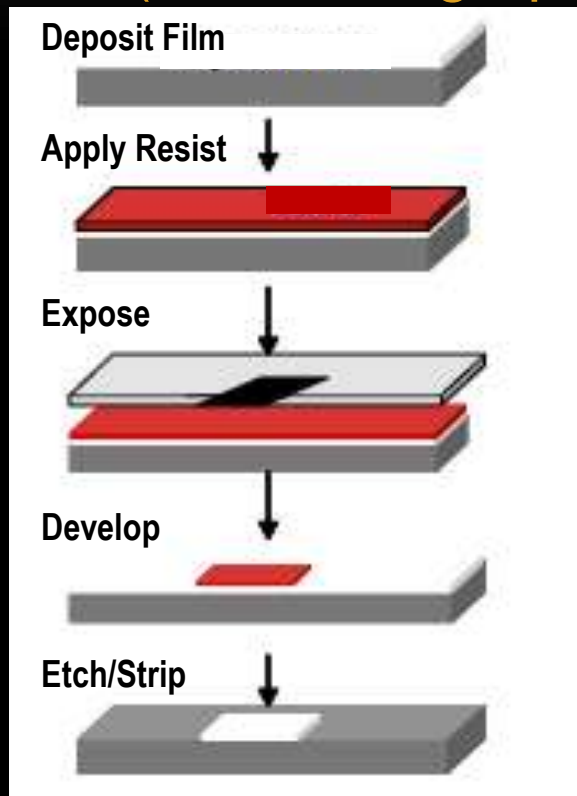
High Performance Computing



Carbon
Electronics

WHY PRINT ELECTRONICS?

Subtractive Process (Photolithography)



Additive Process (Printing)



- *Less steps*
- *Less waste*
- *Lower cost*
- *Short cycle time*

OVERCOMING THE BARRIERS TO ADOPTION

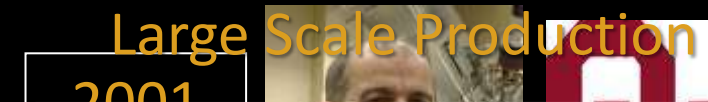
- Quality and Consistency
 - Availability
 - Cost
 - Purity
 - Other Carbon Forms
 - Residual catalyst
 - Chiral Mixture
 - Handling
 - Processing / Printing
-

MANUFACTURING PLATFORM

2008

Large Scale Production

2001



2009

TSCA Listing



Norman, OK

Apps Dev Ctr



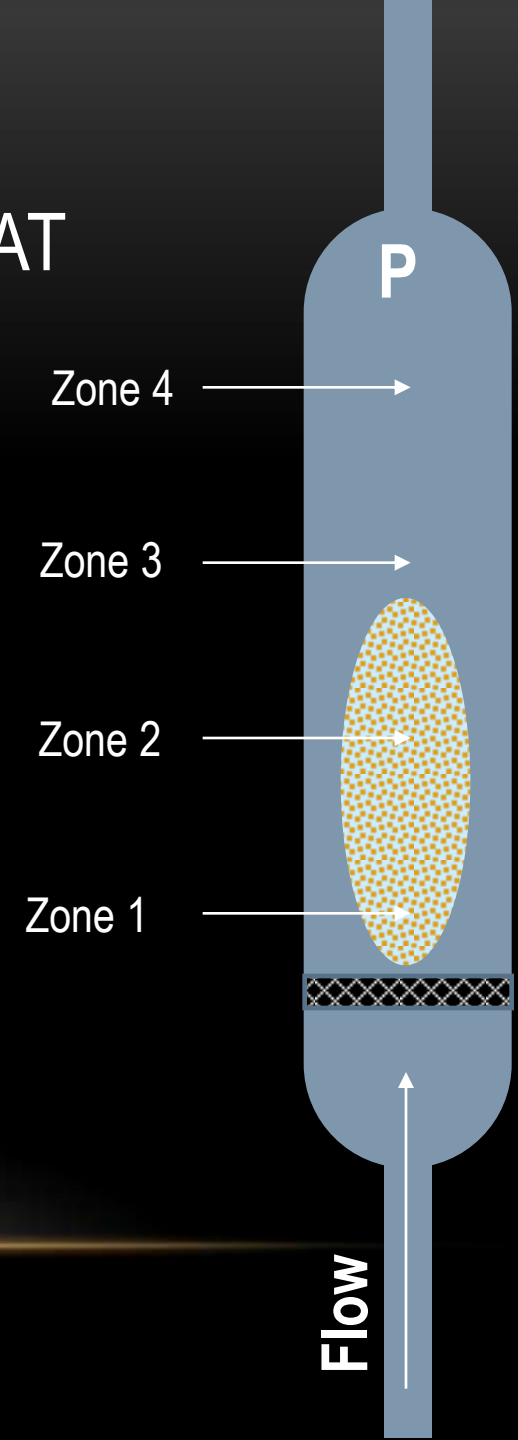
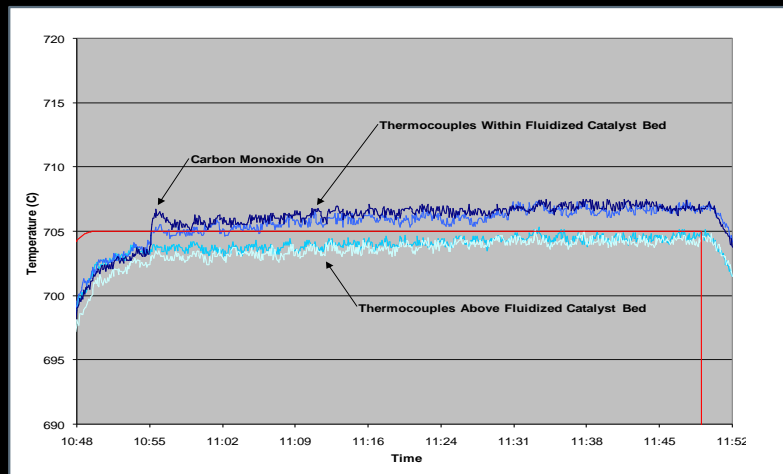
Canton, MA

OVERCOMING THE BARRIERS TO ADOPTION

- Quality and Consistency
 - Availability
 - Cost
 - Purity
 - Other Carbon Forms
 - Residual catalyst
 - Chiral Mixture
 - Handling
 - Processing / Printing
-

TECHNOLOGY PLATFORM - CoMoCAT

- CO disproportionation ($2 \text{CO} \rightarrow \text{C} + \text{CO}_2$)
- Supported transition metal catalysts
- Fluidized bed for uniformity
- Moderate temperatures (700 – 900°C) with precise control ($\pm 1^\circ \text{C}$)
- Moderate pressures = 1 – 10 atm



CUSTOMIZATION OF SWCNT

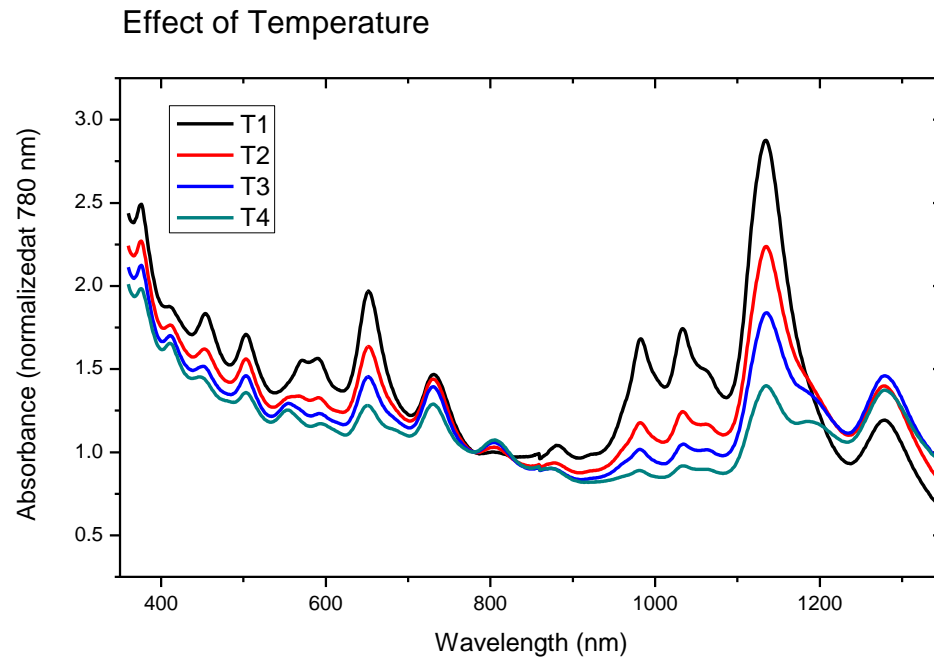
Variables

- Temperature
- Pressure
- Catalyst Composition
- Gas composition

Effects

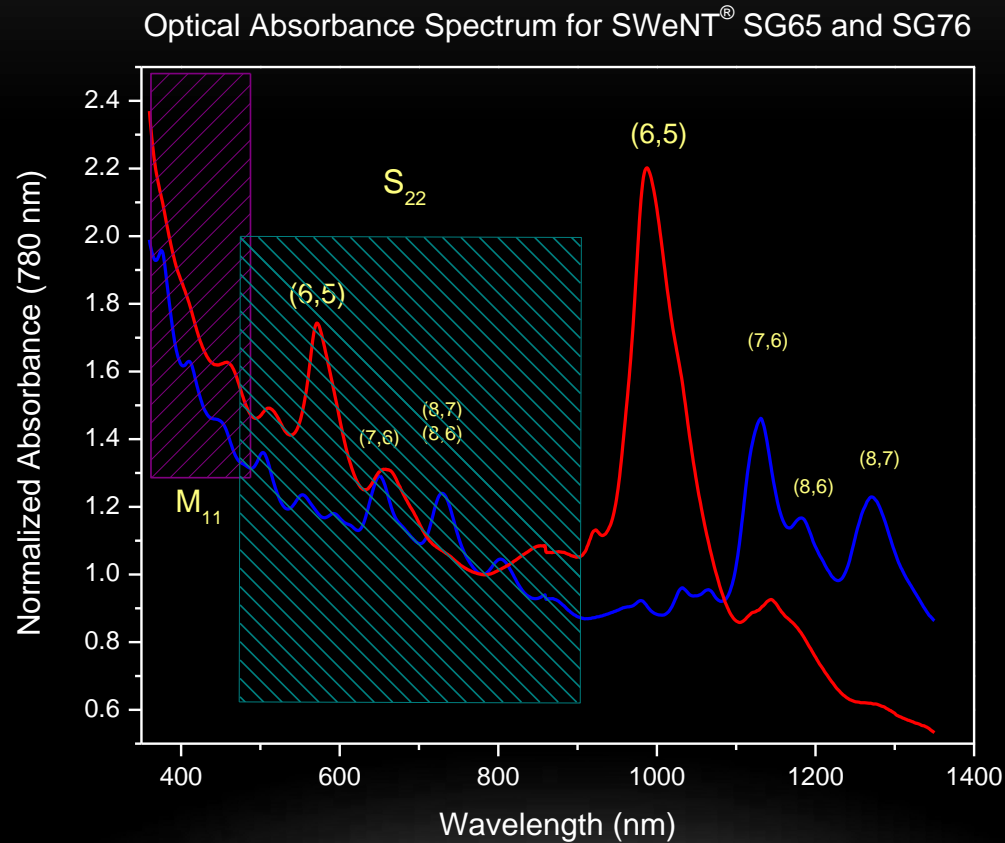
- Diameter Control and Distribution
- Tube Length
- Bundle Size
- Purity

EFFECT OF TEMPERATURE



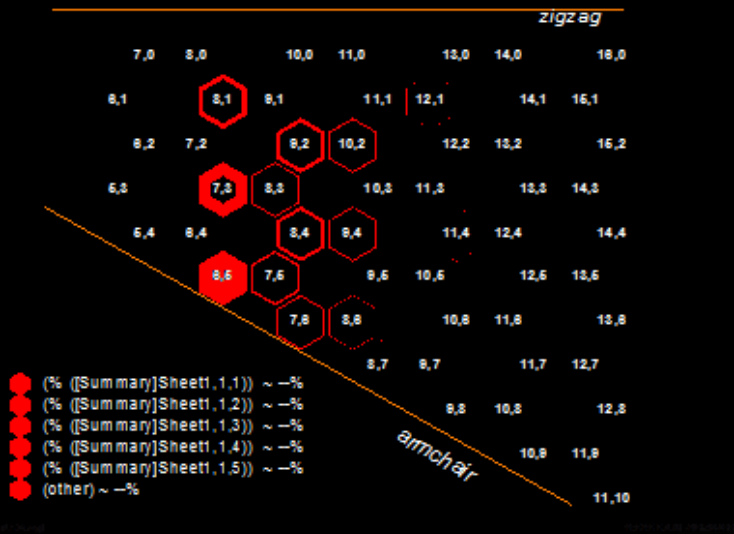
QUALITY MEASUREMENTS

OPTICAL ABSORBANCE SPECTRA

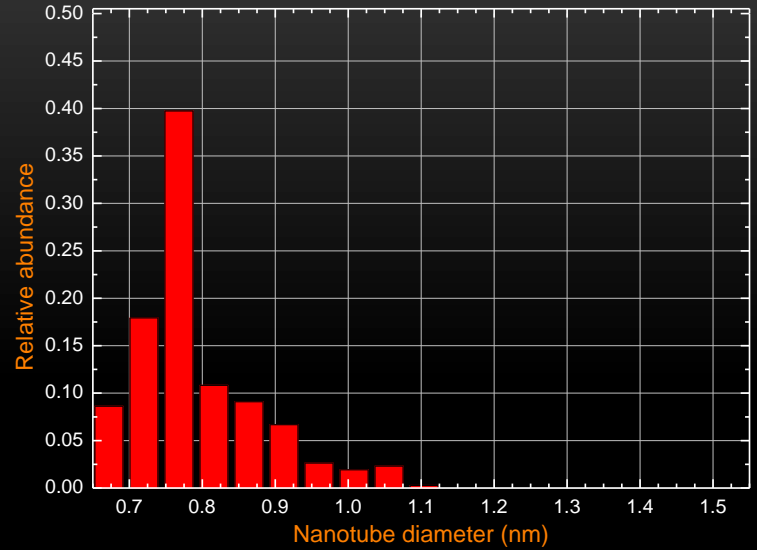


QUALITY MEASUREMENTS

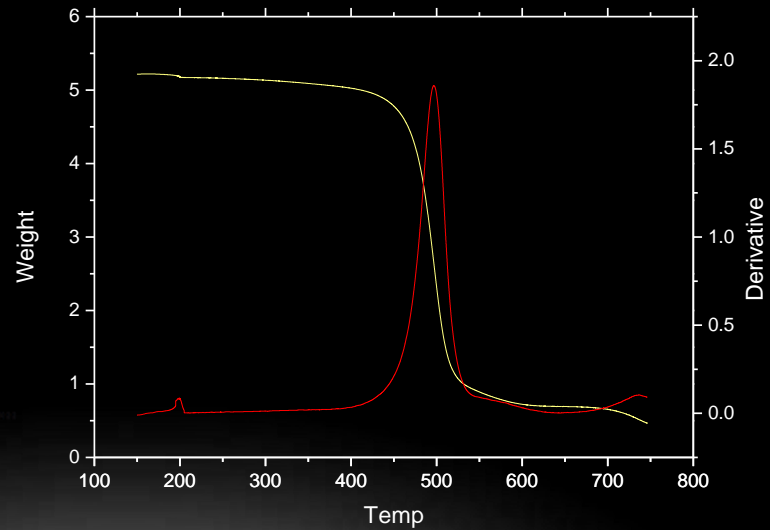
Distribution of n,m Species for SG65



Diameter Distribution from Fluorescence Analysis



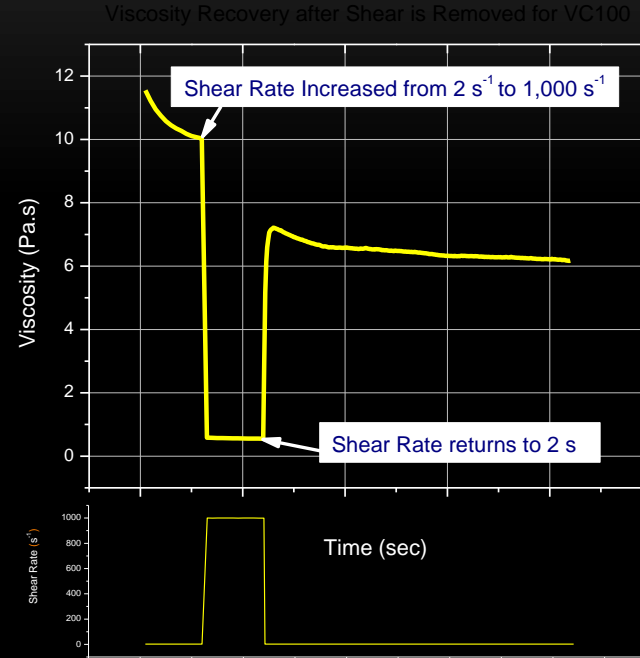
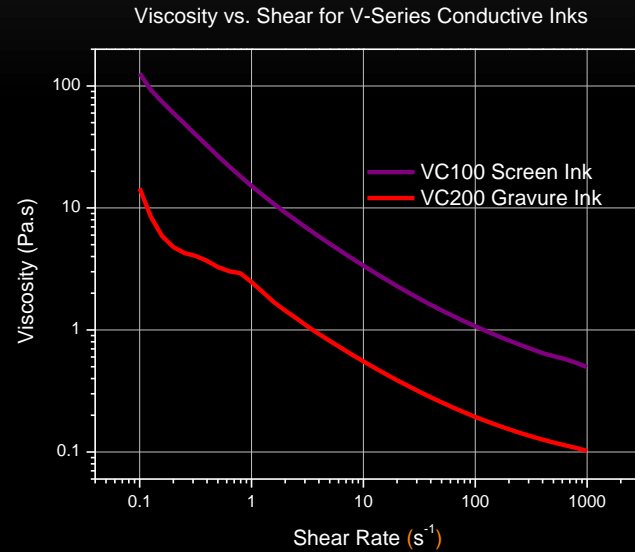
TGA for SG76



OVERCOMING THE BARRIERS TO ADOPTION

- Quality and Consistency
 - Availability
 - Cost
 - Purity
 - Other Carbon Forms
 - Residual catalyst
 - Chiral Mixture
 - Handling
 - Processing / Printing
-

RHEOLOGY OF V-SERIES SCREEN AND GRAVURE INKS



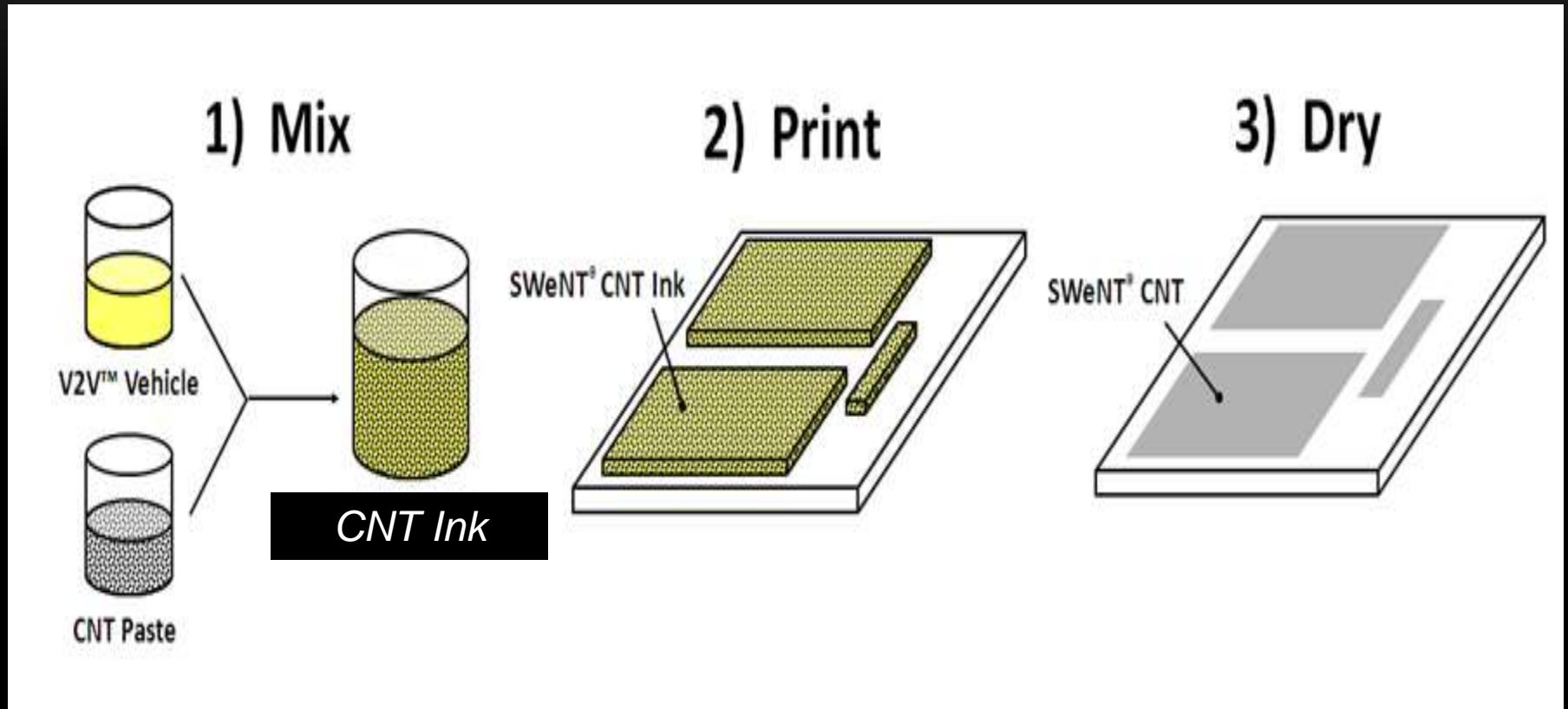
Recovery to 80% of original viscosity ~7 seconds after reduction of shear rate



Courtesy Dr. Erika Rebrosova, Western Michigan University



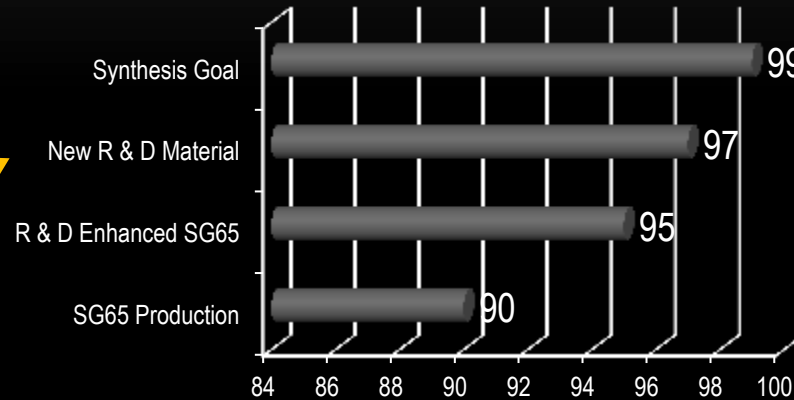
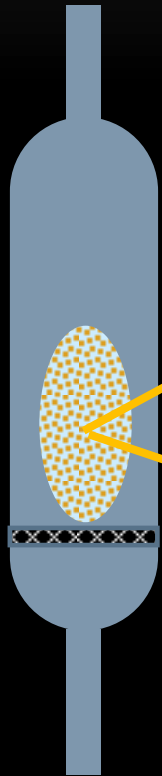
V2V™ INK TECHNOLOGY*



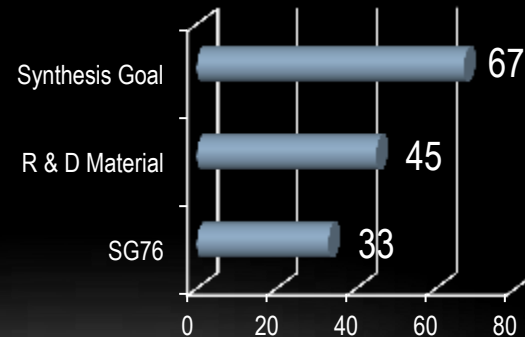
CNTs can be printed using Standard Industrial Printing Equipment

SWCNT TAILORED FOR APPLICATIONS

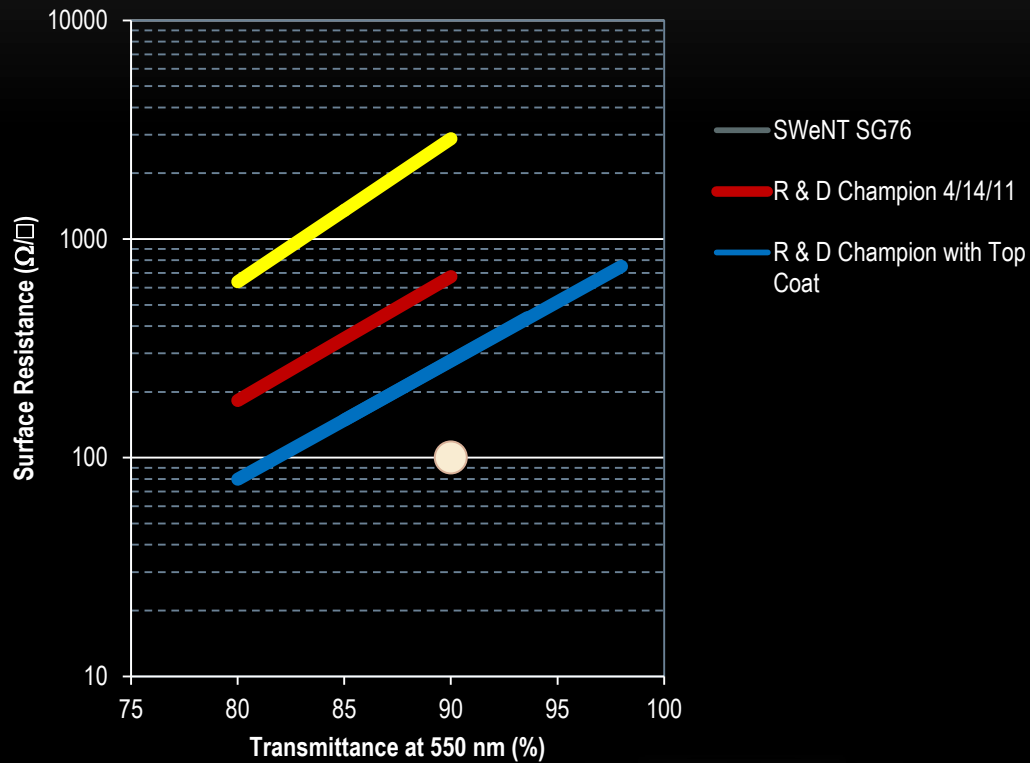
Semiconducting Enriched for TFTs



Metallic Enriched for TCF Electrodes etc.



METALLIC ENRICHED FOR TCF



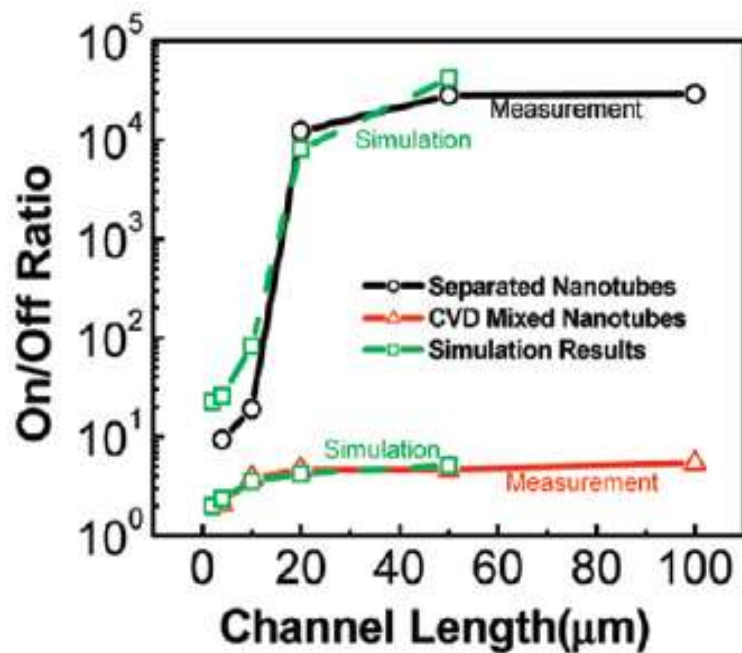
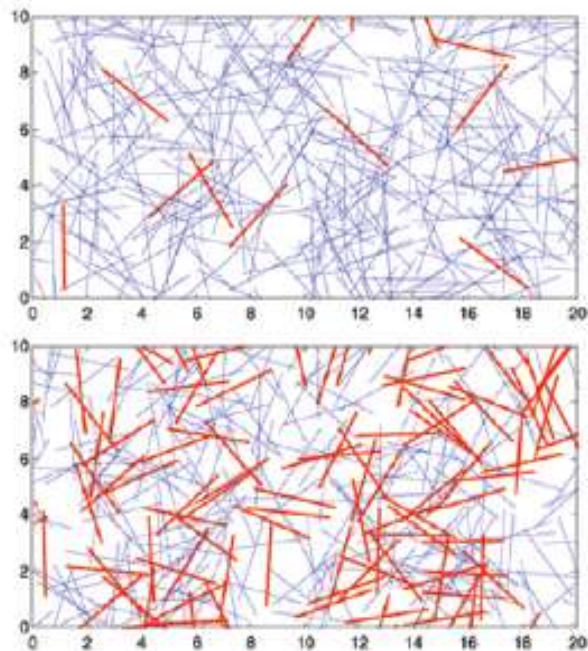
269 ohm/sq @
89.7% VLT



Our Champion Sample
(April 2011)

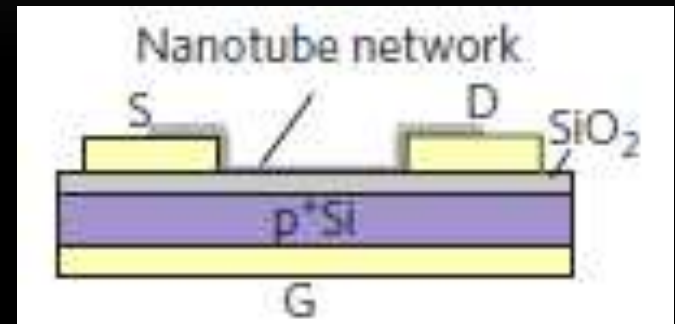
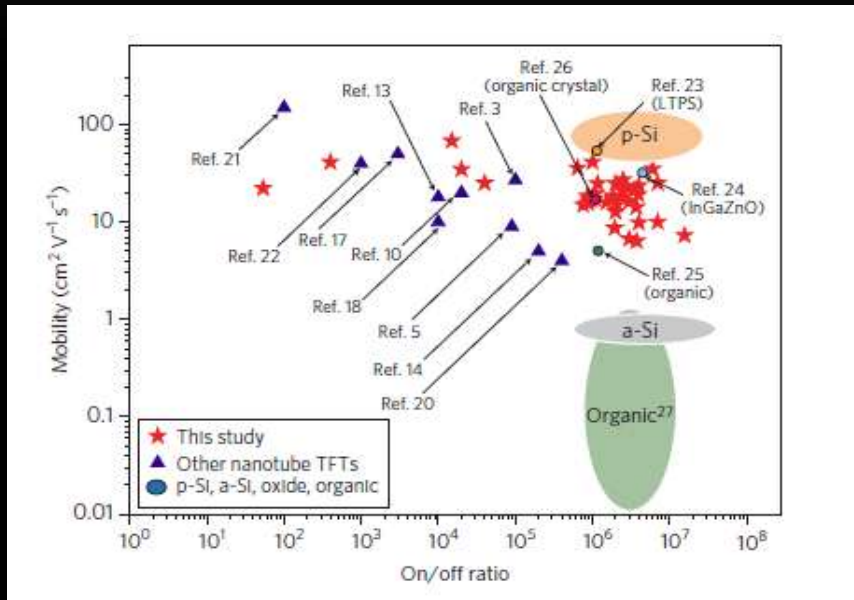
CNT TFTs

ref. Zhou et al, Nano Lett. 9, 4285 (2009)



Red = Metallic CNT
Gray = SC CNT

FLEXIBLE, HIGH PERFORMANCE CARBON NANOTUBE INTEGRATED CIRCUITS

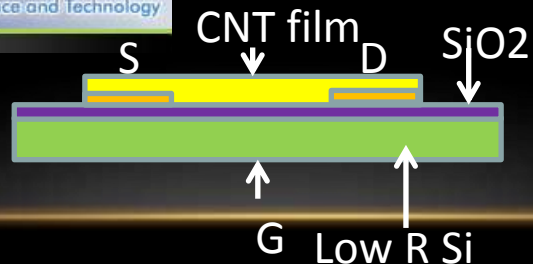


CNT TFTs can have 100X higher Mobility than a-Si and Organic semiconductors!

Ref. Sun, D.M. et. al. *Nature Nanotechnology Letts* 6, 156–161 (2011).

SEMICONDUCTING ENRICHED SWCNT INKS FOR PRINTING THIN FILM TRANSISTORS

Raw material	Max ON/OFF	Max Mobility cm ² /V.s	Channel L μm	Channel W μm
Goal	>10 ⁶	> 10 cm ² /V/s	20 – 40 μm	40 – 80 μm
Current Commercial SWCNT	10 ⁵	> 10 cm ² /V/s	35	50 - 150



Cross-Sectional View of BSI Test TFT





THANK YOU

QUESTIONS?

